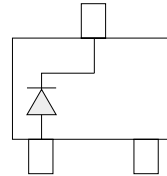


## SWITCHING DIODE

### FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

MARKING : A6



## BAS16



MAXIMUM RATINGS (TA=25°C unless otherwise noted)

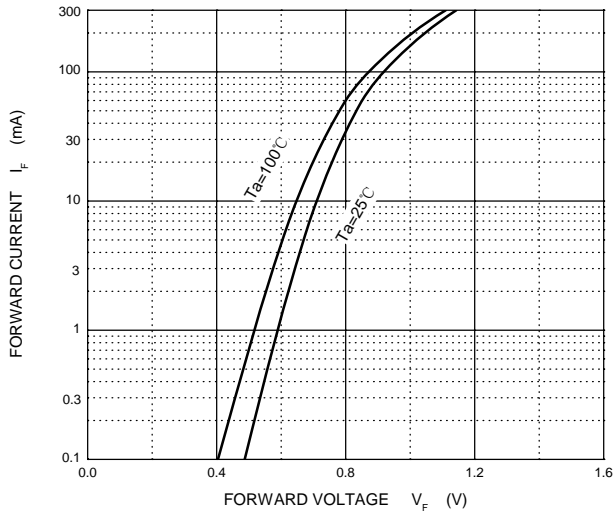
Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V <sub>RM</sub>	100	V
Peak Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	75	V
Working Peak Reverse Voltage	V <sub>RWM</sub>		
DC Blocking Voltage	V <sub>R</sub>		
RMS Reverse Voltage	V <sub>R(RMS)</sub>	53	V
Forward Continuous Current	I <sub>FM</sub>	300	mA
Average Rectified Output Current	I <sub>O</sub>	150	mA
Peak Forward Surge Current @t=1.0μs	I <sub>FSM</sub>	2.0	A
		@t=1.0s	
Power Dissipation	P <sub>D</sub>	225	mW
Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	556	°C/W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55~+150	°C

Electrical Ratings @TA=25°C

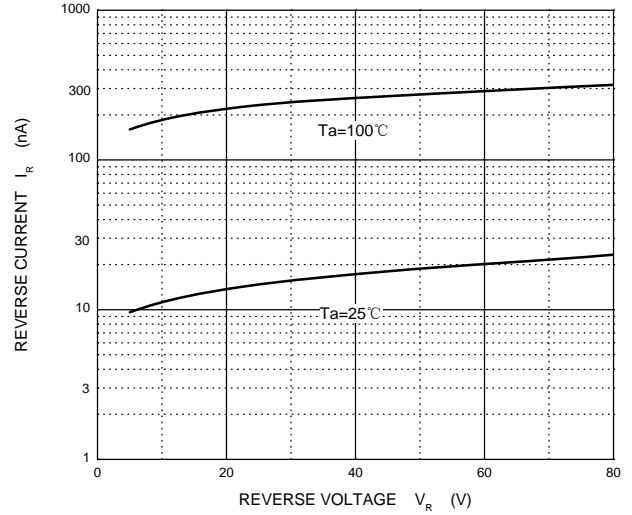
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	V <sub>(BR)</sub>	I <sub>R</sub> = 100μA	75		V
Reverse voltage leakage current	I <sub>R</sub>	V <sub>R</sub> =75V		1	μA
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =1mA		0.715	V
		I <sub>F</sub> =10mA		0.855	
		I <sub>F</sub> =50mA		1	
Diode capacitance	C <sub>D</sub>	V <sub>R</sub> =0, f=1MHz		2	pF
Reveres recovery time	t <sub>rr</sub>	I <sub>F</sub> =I <sub>R</sub> =10mA, I <sub>rr</sub> =0.1×I <sub>R</sub> , R <sub>L</sub> =100Ω		6	ns

## BAS16 Typical Characteristics

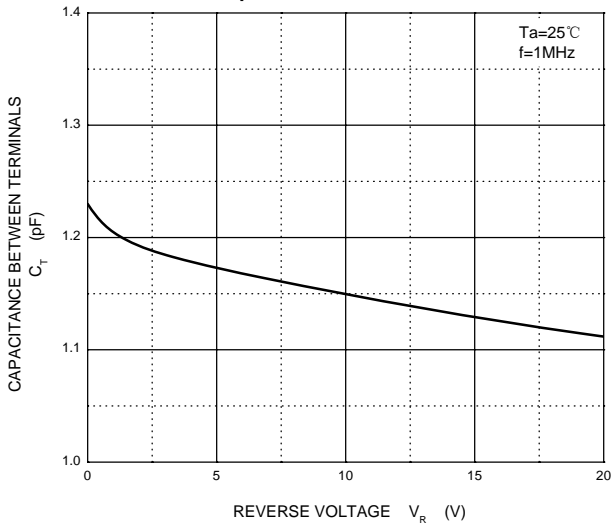
**Forward Characteristics**



**Reverse Characteristics**



**Capacitance Characteristics**



**Power Derating Curve**

